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**IGBT** 

## SGF5N150UF

## **General Description**

Fairchild's Insulated Gate Bipolar Transistor (IGBT) provides low conduction and switching losses. SGF5N150UF is designed for the Switching Power Supply applications.

## **Features**

- High Speed Switching
- Low Saturation Voltage :  $V_{CE(sat)} = 4.7 \text{ V} @ I_C = 5A$
- High Input Impedance

## **Application**

Switching Power Supply - High Input Voltage Off-line Converter





## **Absolute Maximum Ratings** $T_C = 25^{\circ}C$ unless otherwise noted

| Symbol              | Description                                                             |                          | SGF5N150UF  | Units |  |
|---------------------|-------------------------------------------------------------------------|--------------------------|-------------|-------|--|
| V <sub>CES</sub>    | Collector-Emitter Voltage                                               |                          | 1500        | V     |  |
| V <sub>GES</sub>    | Gate-Emitter Voltage                                                    |                          | ± 20        | V     |  |
| _                   | Collector Current                                                       | @ T <sub>C</sub> = 25°C  | 10          | А     |  |
| IC                  | Collector Current                                                       | @ T <sub>C</sub> = 100°C | 5           | А     |  |
| I <sub>CM (1)</sub> | Pulsed Collector Current                                                |                          | 20          | А     |  |
| P <sub>D</sub>      | Maximum Power Dissipation                                               | $@ T_C = 25^{\circ}C$    | 62.5        | W     |  |
|                     | Maximum Power Dissipation                                               | @ T <sub>C</sub> = 100°C | 25          | W     |  |
| T <sub>J</sub>      | Operating Junction Temperature                                          |                          | -55 to +150 | °C    |  |
| T <sub>stg</sub>    | Storage Temperature Range                                               |                          | -55 to +150 | °C    |  |
| T <sub>L</sub>      | Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds |                          | 300         | °C    |  |

#### Notes :

(1) Repetitive rating : Pulse width limited by max. junction temperature

## **Thermal Characteristics**

| Symbol          | Parameter                               | Тур. | Max. | Units |
|-----------------|-----------------------------------------|------|------|-------|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case    |      | 2.0  | °C/W  |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient |      | 40   | °C/W  |

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| Symbol              | Parameter                                     | Test Conditions                                        | Min. | Тур. | Max.  | Units |
|---------------------|-----------------------------------------------|--------------------------------------------------------|------|------|-------|-------|
| Off Cha             | racteristics                                  |                                                        |      |      |       |       |
| BV <sub>CES</sub>   | Collector-Emitter Breakdown Voltage           | $V_{GE} = 0V, I_{C} = 1mA$                             | 1500 |      |       | V     |
| I <sub>CES</sub>    | Collector Cut-Off Current                     | $V_{CE} = V_{CES}, V_{GE} = 0V$                        |      |      | 1.0   | mA    |
| I <sub>GES</sub>    | G-E Leakage Current                           | $V_{GE} = V_{GES}, V_{CE} = 0V$                        |      |      | ± 100 | nA    |
| On Char             | racteristics                                  |                                                        |      |      |       |       |
| V <sub>GE(th)</sub> | G-E Threshold Voltage                         | $I_C = 5mA$ , $V_{CE} = V_{GE}$                        | 2.0  | 3.0  | 4.0   | V     |
|                     | Collector to Emitter                          |                                                        |      | 4 -  |       |       |
| $V_{CE(sat)}$       | Saturation Voltage $I_C = 5A$ , $V_{GE} = 5A$ |                                                        |      | 4.7  | 5.5   | V     |
| C <sub>ies</sub>    | Input Capacitance                             | V <sub>CE</sub> = 10V V <sub>CE</sub> = 0V.            |      | 780  |       |       |
| C <sub>ies</sub>    | Input Capacitance                             | $V_{CE} = 10V, V_{GE} = 0V,$                           |      | 780  |       | рF    |
| C <sub>oes</sub>    | Output Capacitance                            |                                                        |      | 130  |       | pF    |
| C <sub>res</sub>    | Reverse Transfer Capacitance                  |                                                        |      | 70   |       | pF    |
| Switchir            | ng Characteristics                            |                                                        |      |      |       |       |
| t <sub>d(on)</sub>  | Turn-On Delay Time                            |                                                        |      | 10   |       | ns    |
| t <sub>r</sub>      | Rise Time                                     | $V_{CC} = 600 \text{ V}$<br>$I_{C} = 5\text{A}$        |      | 15   |       | ns    |
| t <sub>d(off)</sub> | Turn-Off Delay Time                           | $R_{\rm G} = 10\Omega$                                 |      | 30   | 50    | ns    |
| t <sub>f</sub>      | Fall Time                                     | $R_{G} = 10\Omega$<br>- $V_{GF} = 10V$                 |      | 70   | 120   | ns    |
| E <sub>on</sub>     | Turn-On Switching Loss                        | Inductive Load                                         |      | 190  |       | uJ    |
| E <sub>off</sub>    | Turn-Off Switching Loss                       | T <sub>C</sub> = 25°C                                  |      | 100  |       | uJ    |
| E <sub>ts</sub>     | Total Switching Loss                          | -                                                      |      | 290  | 580   | uJ    |
| $Q_g$               | Total Gate Charge                             | $V_{CF} = 600 \text{ V}, I_{C} = 5\text{A}$            |      | 30   | 45    | nC    |
| $Q_{ge}$            | Gate-Emitter Charge                           | $V_{CE} = 000 \text{ V}, V_{C} = 3A$<br>$V_{GF} = 10V$ |      | 3    | 5     | nC    |
| Q <sub>gc</sub>     | Gate-Collector Charge                         | *GE = 10 V                                             |      | 15   | 25    | nC    |

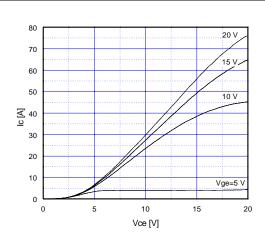


Fig 1. Typical Output Characteristics

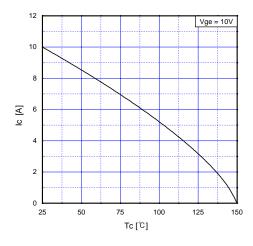


Fig 3. Maximum Collector Current vs. Case Temperature

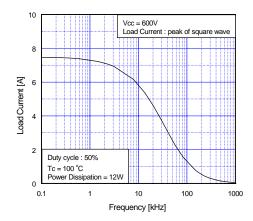


Fig 5. Load Current vs. Frequency

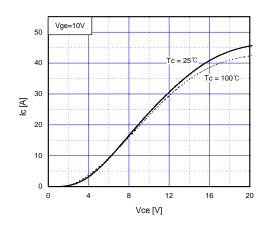


Fig 2. Typical Output Characteristics

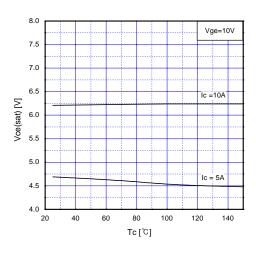


Fig 4. Saturation Voltage vs. Case Temperature

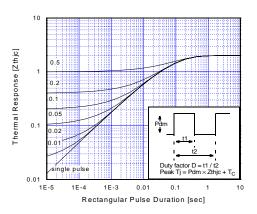
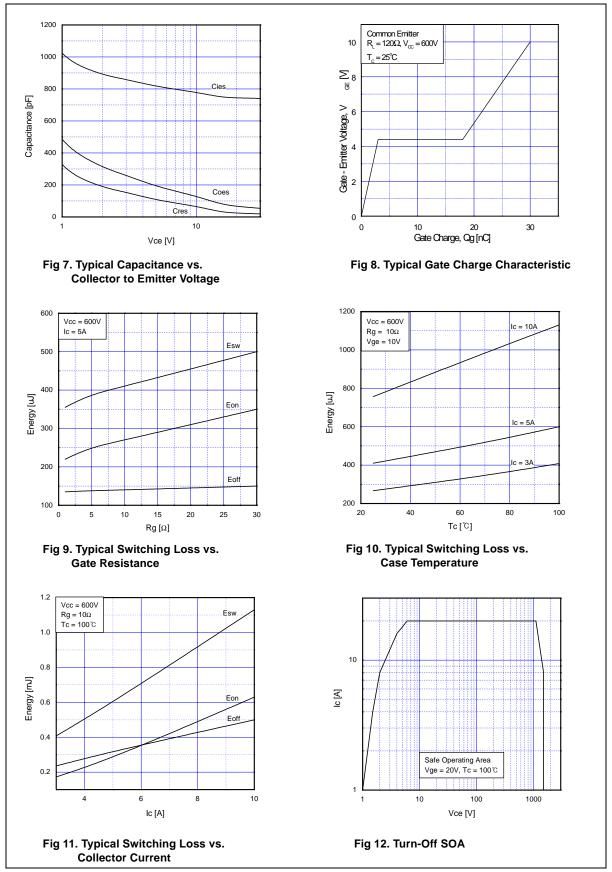
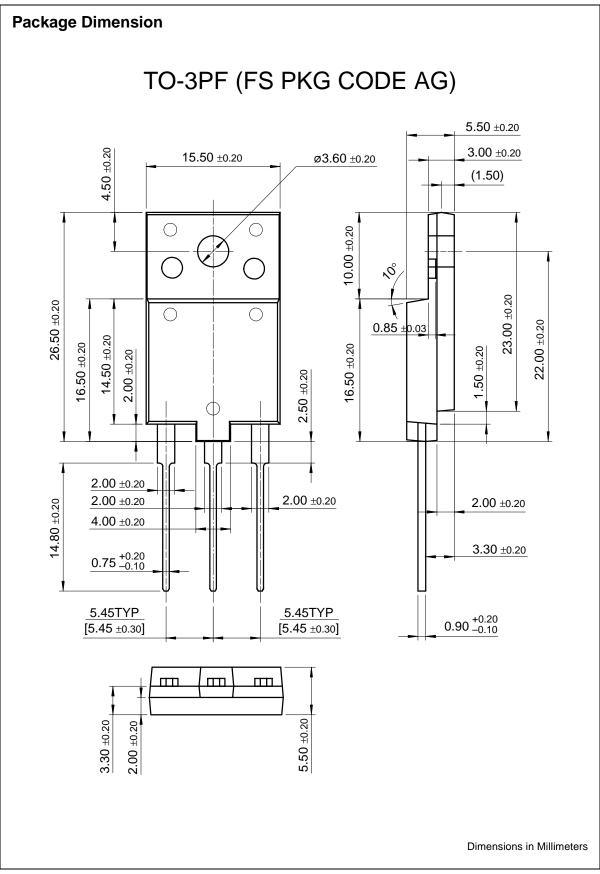


Fig 6. Transient Thermal Impedance of IGBT Junction to Case

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